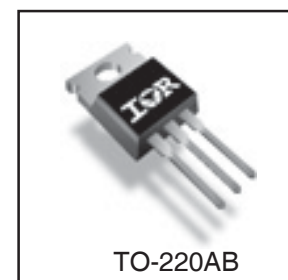
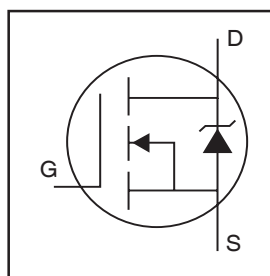


Features

- Key parameters optimized for Class-D audio amplifier applications
- Low $R_{DS(ON)}$ for improved efficiency
- Low Q_G and Q_{SW} for better THD and improved efficiency
- Low Q_{RR} for better THD and lower EMI
- 175°C operating junction temperature for ruggedness
- Can deliver up to 300W per channel into 8Ω load in half-bridge topology

Key Parameters		
V_{DS}	200	V
$R_{DS(ON)}$ typ. @ 10V	139	mΩ
Q_g typ.	25	nC
Q_{sw} typ.	15	nC
$R_{G(int)}$ typ.	1.0	Ω
T_J max	175	°C



Description

This Digital Audio MOSFET is specifically designed for Class-D audio amplifier applications. This MOSFET utilizes the latest processing techniques to achieve low on-resistance per silicon area. Furthermore, Gate charge, body-diode reverse recovery and internal Gate resistance are optimized to improve key Class-D audio amplifier performance factors such as efficiency, THD and EMI. Additional features of this MOSFET are 175°C operating junction temperature and repetitive avalanche capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for ClassD audio amplifier applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	200	V
V_{GS}	Gate-to-Source Voltage	±30	
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	17	A
I_D @ $T_C = 100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	12	
I_{DM}	Pulsed Drain Current ①	68	
P_D @ $T_C = 25^\circ C$	Power Dissipation ④	140	W
P_D @ $T_C = 100^\circ C$	Power Dissipation ④	71	
	Linear Derating Factor	0.95	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

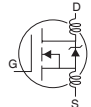
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	1.05	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ④	—	62	

IRFB4103PbF

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.21	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	139	165	m Ω	$V_{GS} = 10V, I_D = 12A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-13	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 200V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$
g_{fs}	Forward Transconductance	7.1	—	—	S	$V_{DS} = 50V, I_D = 12A$
Q_g	Total Gate Charge	—	25	38	nC	$V_{DS} = 160V$ $V_{GS} = 10V$ $I_D = 12A$ See Fig. 6 and 19
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	5.4	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	2.9	—		
Q_{gd}	Gate-to-Drain Charge	—	12	—		
Q_{godr}	Gate Charge Overdrive	—	4.7	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	15	—		
$R_{G(int)}$	Internal Gate Resistance	—	1.0	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	9.6	—	ns	$V_{DD} = 100V, V_{GS} = 10V$ ③ $I_D = 12A$ $R_G = 2.5\Omega$
t_r	Rise Time	—	40	—		
$t_{d(off)}$	Turn-Off Delay Time	—	16	—		
t_f	Fall Time	—	5.4	—		
C_{iss}	Input Capacitance	—	900	—	pF	$V_{GS} = 0V$ $V_{DS} = 50V$ $f = 1.0\text{MHz}$, See Fig.5 $V_{GS} = 0V, V_{DS} = 0V$ to 160V
C_{oss}	Output Capacitance	—	120	—		
C_{rss}	Reverse Transfer Capacitance	—	22	—		
C_{oss}	Effective Output Capacitance	—	150	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		

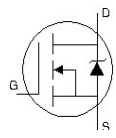


Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	130	mJ
I_{AR}	Avalanche Current ⑤	See Fig. 14, 15, 17a, 17b		A
E_{AR}	Repetitive Avalanche Energy ⑤			mJ

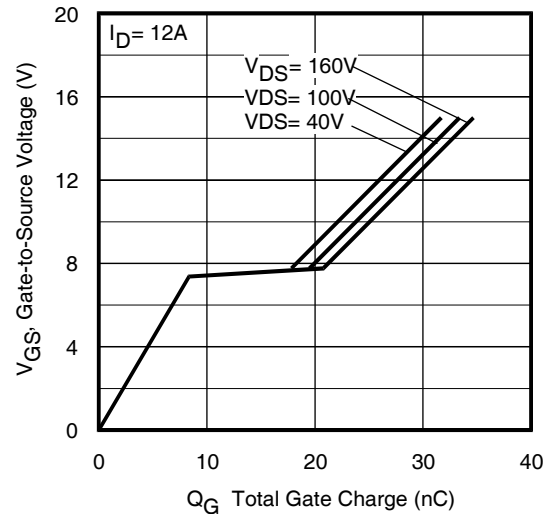
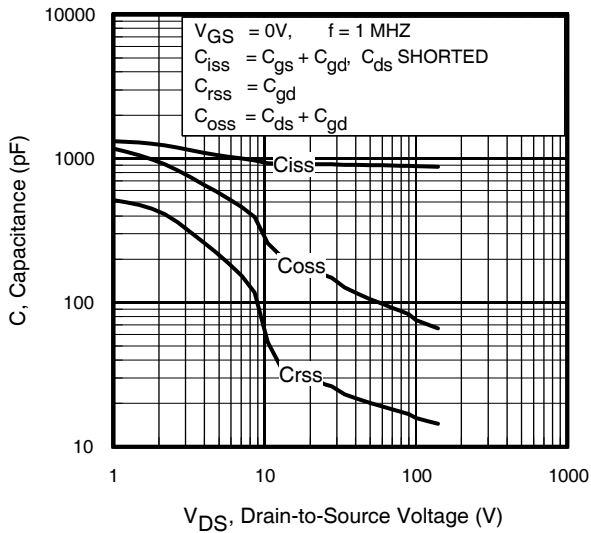
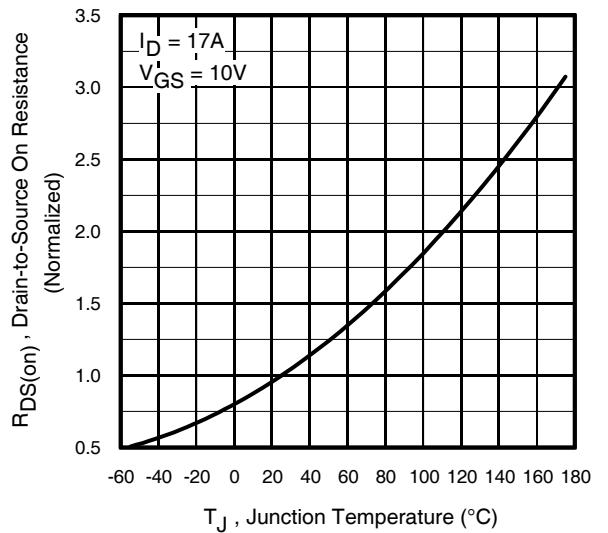
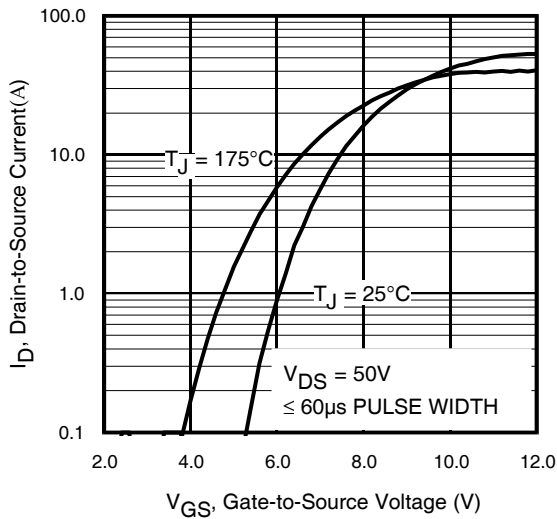
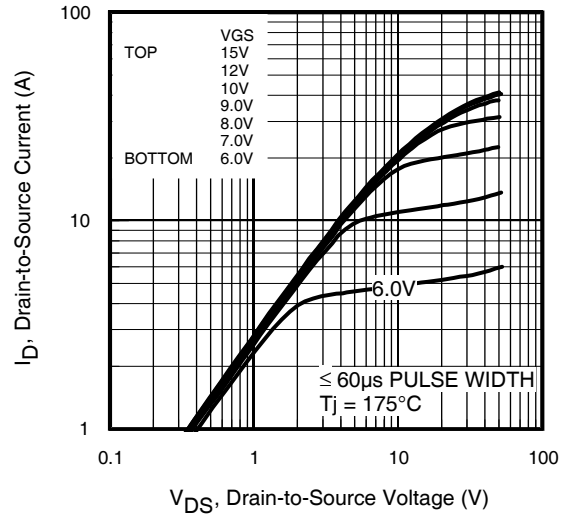
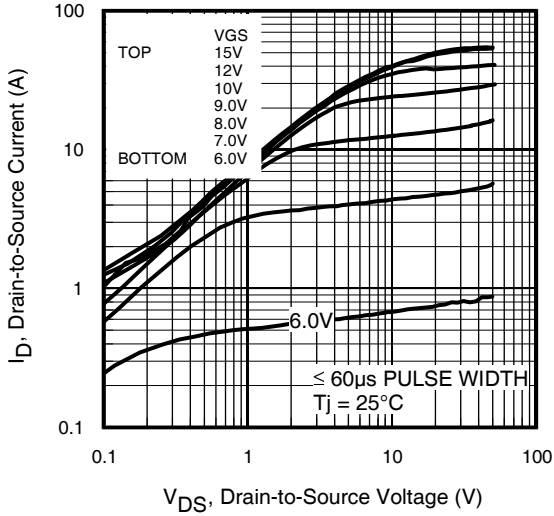
Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S @ T_C = 25^\circ\text{C}$	Continuous Source Current (Body Diode)	—	—	17	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	68		
V_{SD}	Diode Forward Voltage	—	—	1.7	V	$T_J = 25^\circ\text{C}, I_S = 10A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	130	200	ns	$T_J = 25^\circ\text{C}, I_F = 12A$
Q_{rr}	Reverse Recovery Charge	—	730	110	nC	$di/dt = 100A/\mu s$ ③



Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 1.78\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 12A$.
- ③ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ④ R_{θ} is measured at T_J of approximately 90°C .
- ⑤ Limited by T_{jmax} . See Figs. 14, 15, 17a, 17b for repetitive avalanche information



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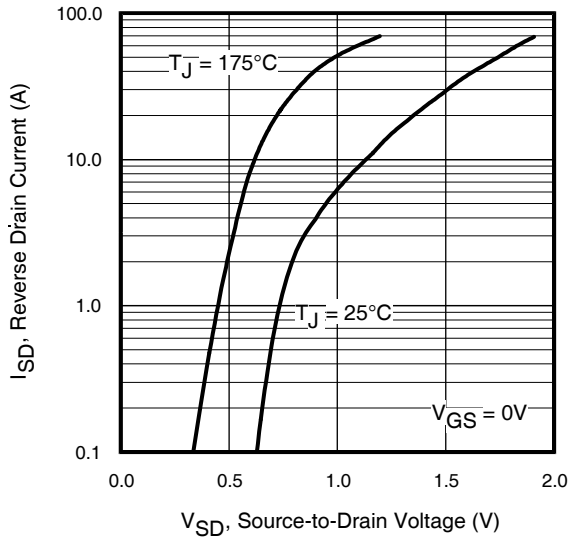


Fig 7. Typical Source-Drain Diode Forward Voltage

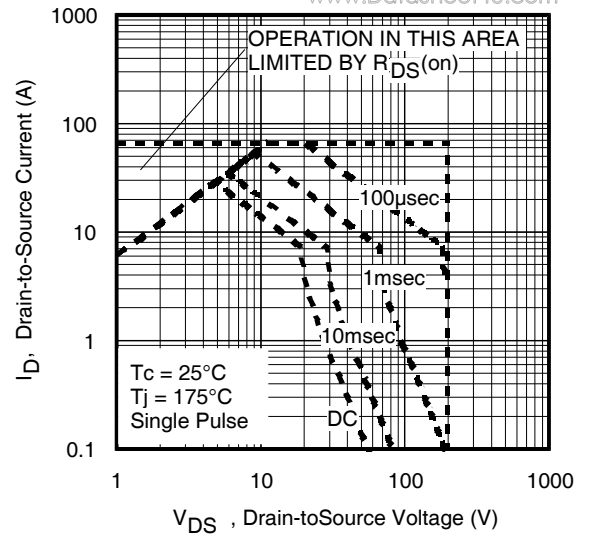


Fig 8. Maximum Safe Operating Area

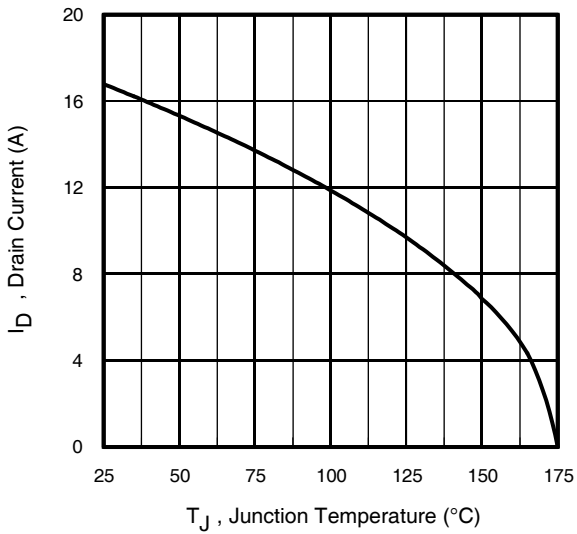


Fig 9. Maximum Drain Current vs. Case Temperature

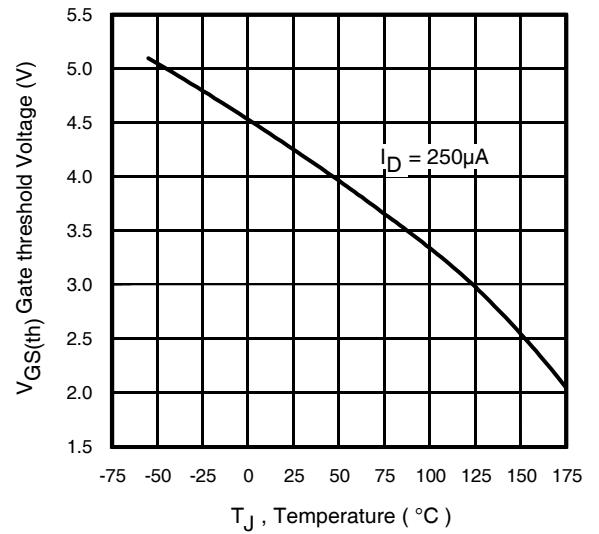


Fig 10. Threshold Voltage vs. Temperature

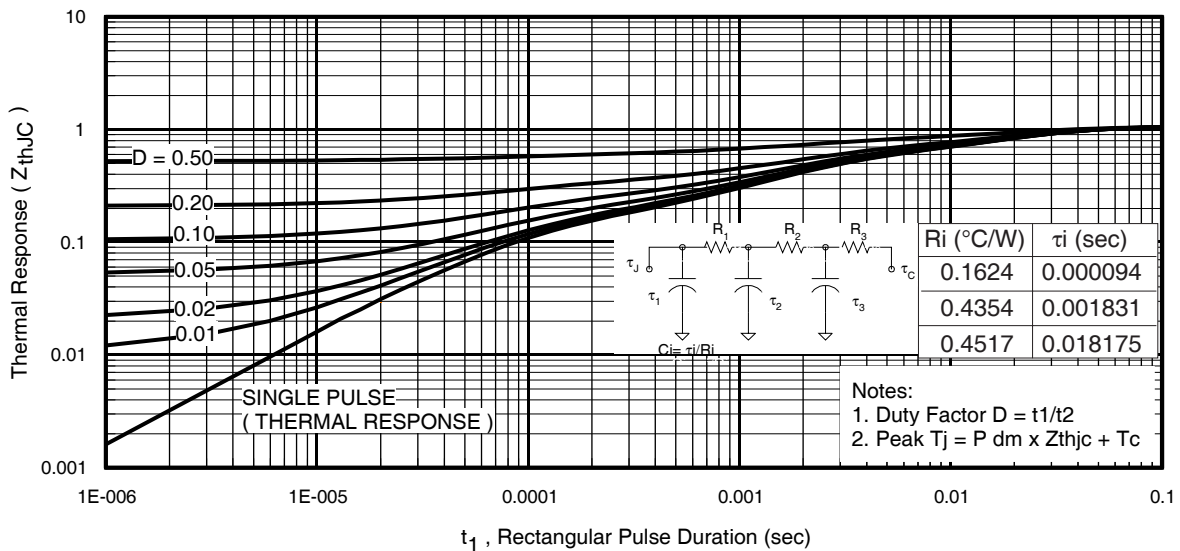


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

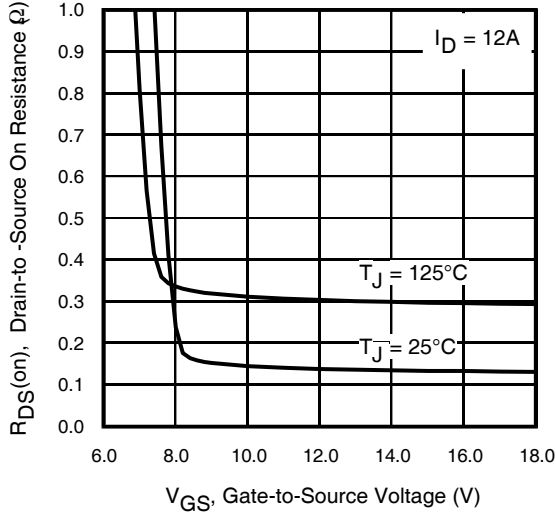


Fig 12. On-Resistance Vs. Gate Voltage

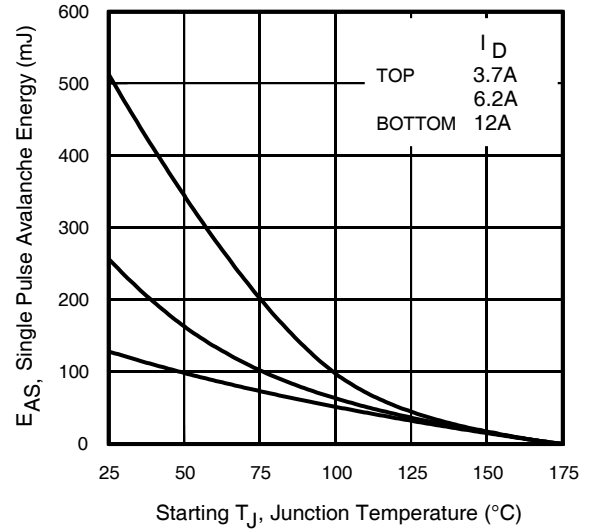


Fig 13. Maximum Avalanche Energy Vs. Drain Current

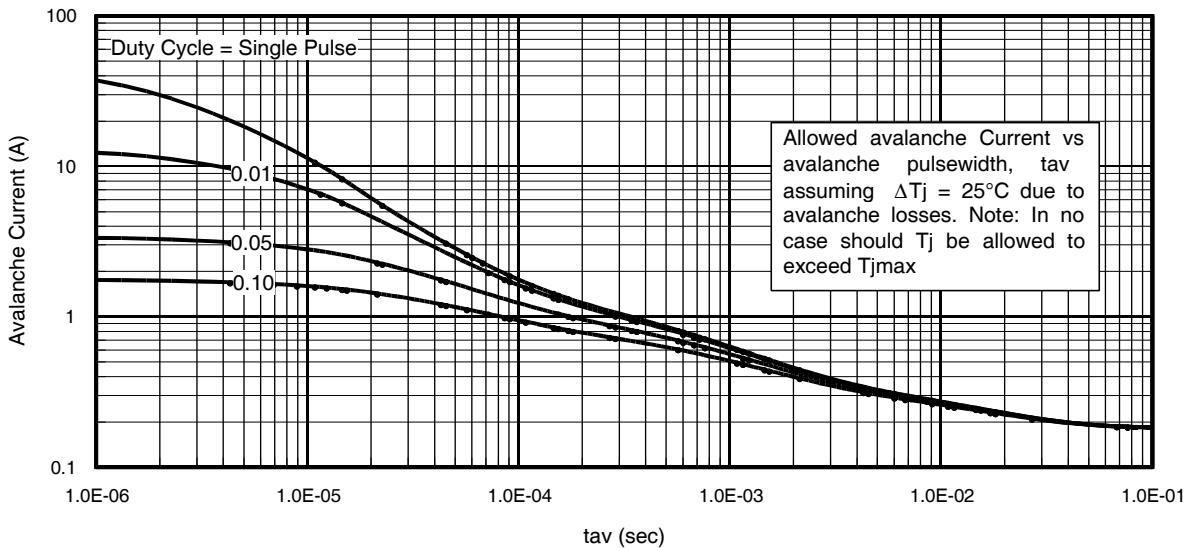
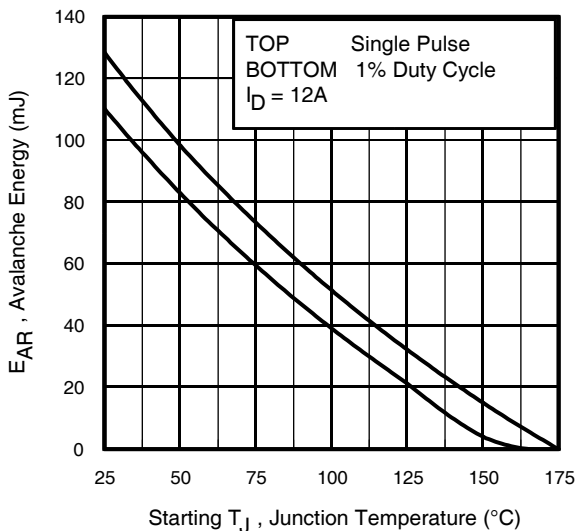


Fig 14. Typical Avalanche Current Vs. Pulsewidth



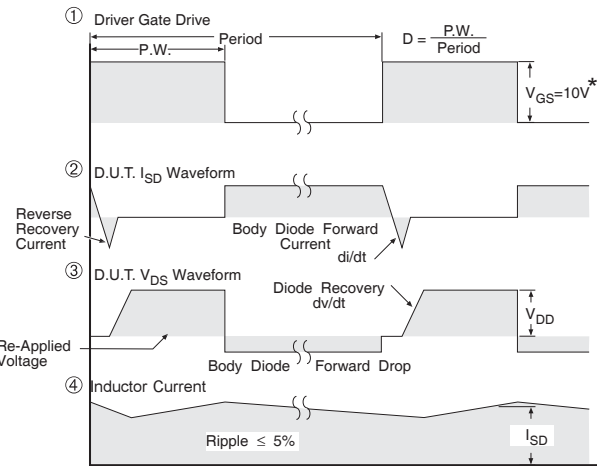
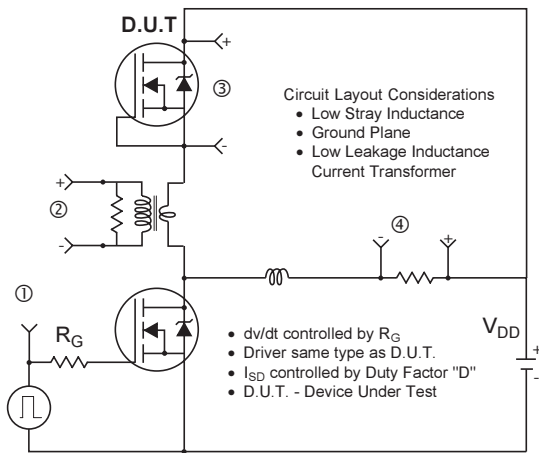
Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 17a, 17b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{thJC}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



* $V_{GS} = 5V$ for Logic Level Devices

Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

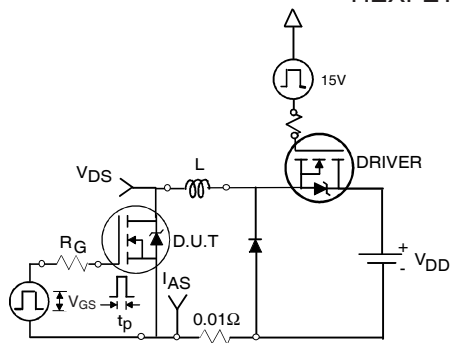


Fig 17a. Unclamped Inductive Test Circuit

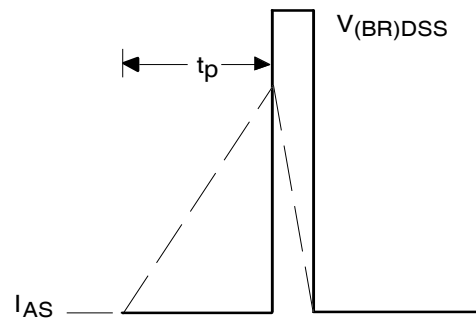


Fig 17b. Unclamped Inductive Waveforms

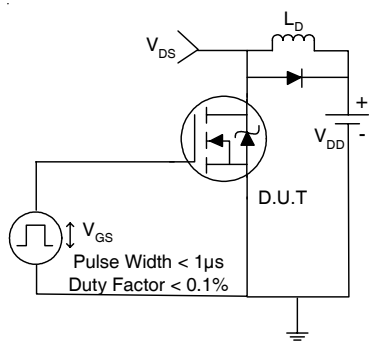


Fig 18a. Switching Time Test Circuit

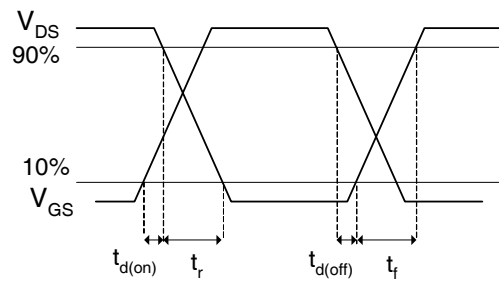


Fig 18b. Switching Time Waveforms

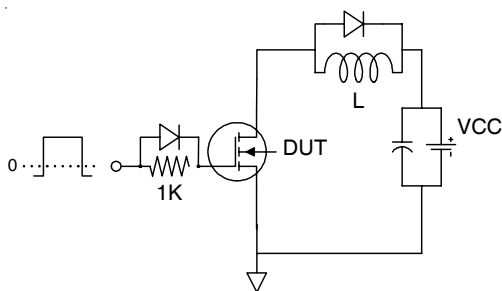


Fig 19a. Gate Charge Test Circuit

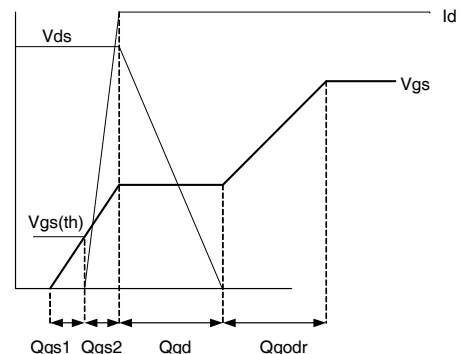
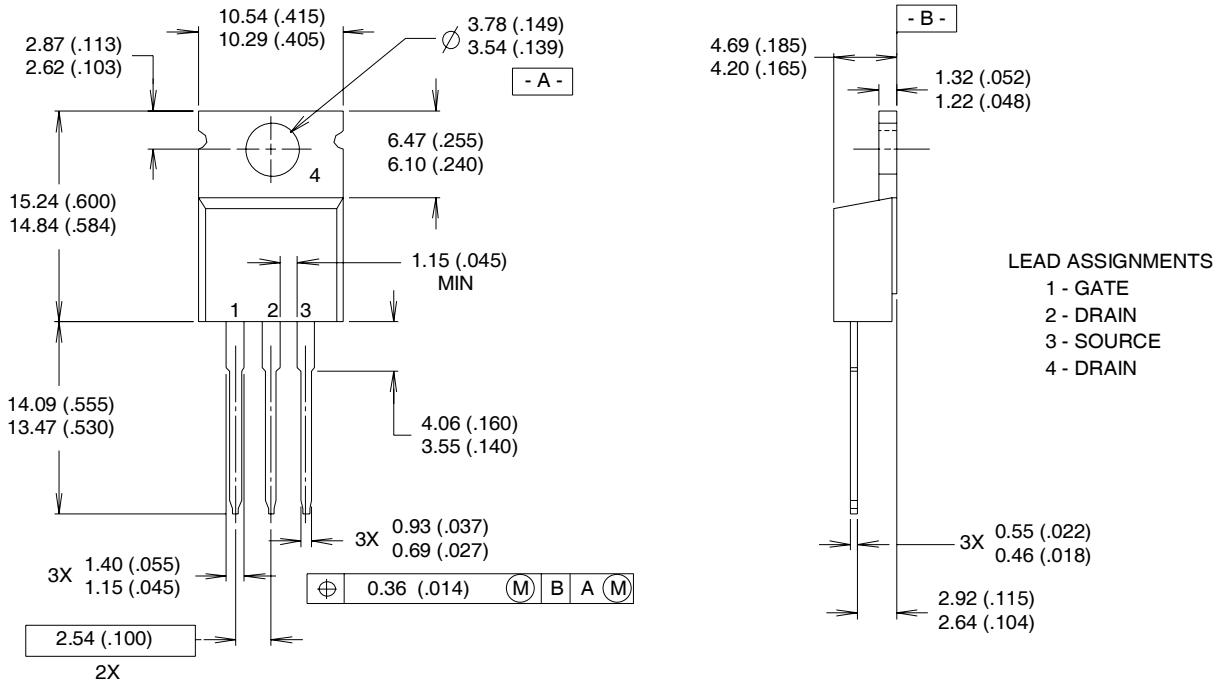


Fig 19b Gate Charge Waveform

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



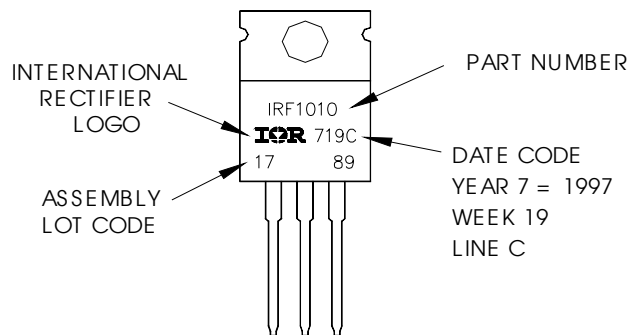
NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH
- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



TO-220AB packages are not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.